

# AN5342FBP, AN5342K

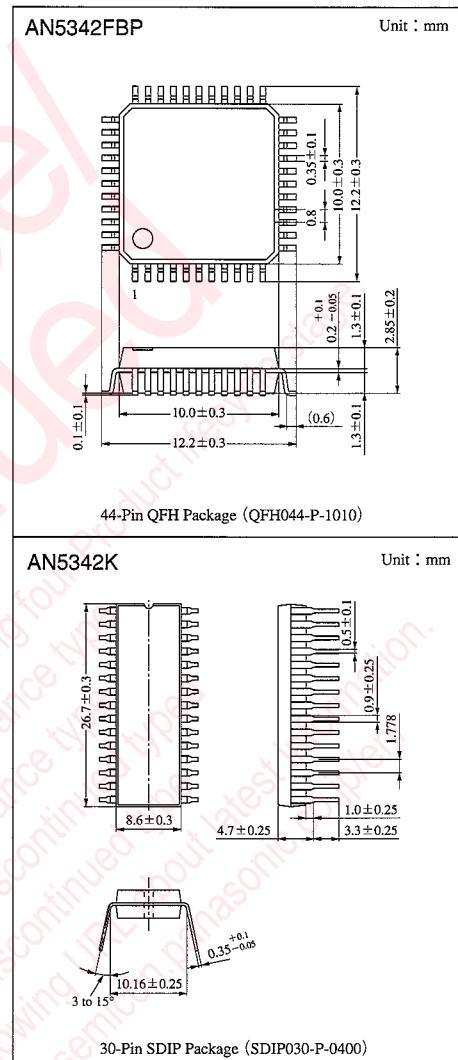
## Color TV Horizontal Aperture Correction IC

### ■ Overview

The AN5342FBP or AN5342K is a horizontal aperture correction IC for color TV. It provides a Y signal waveform with a preshoot or overshoot feature to emphasize horizontal outlines.

### ■ Features

- Including a circuit to add a preshoot or overshoot to a Y signal waveform
- Dynamic sharpness control
- Built-in noise reduction circuit for Y signal
- VM signal output

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### ■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	11	V
Supply current	I <sub>CC</sub>	90	mA
Power dissipation <sup>Note 2)</sup>	P <sub>D</sub>	990	mW
Operating ambient temperature <sup>Note 1)</sup>	T <sub>opr</sub>	-20 to +70	°C
Storage temperature <sup>Note 1)</sup>	T <sub>stg</sub>	-55 to +150	°C

Note 1) Ta=25°C except operating ambient temperature and storage temperature.

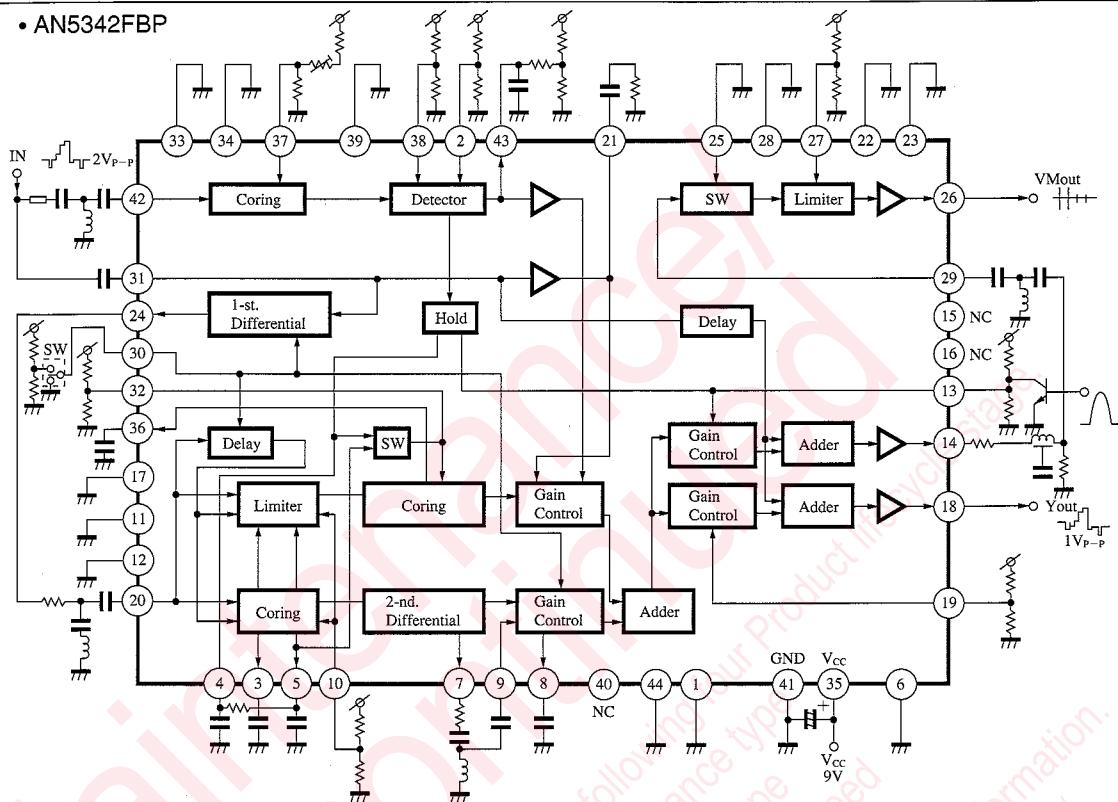
Note 2) For only AN5342FBP, allowable power dissipation of the package at Ta=70°C.

### ■ Recommended Operating Range (Ta=25°C)

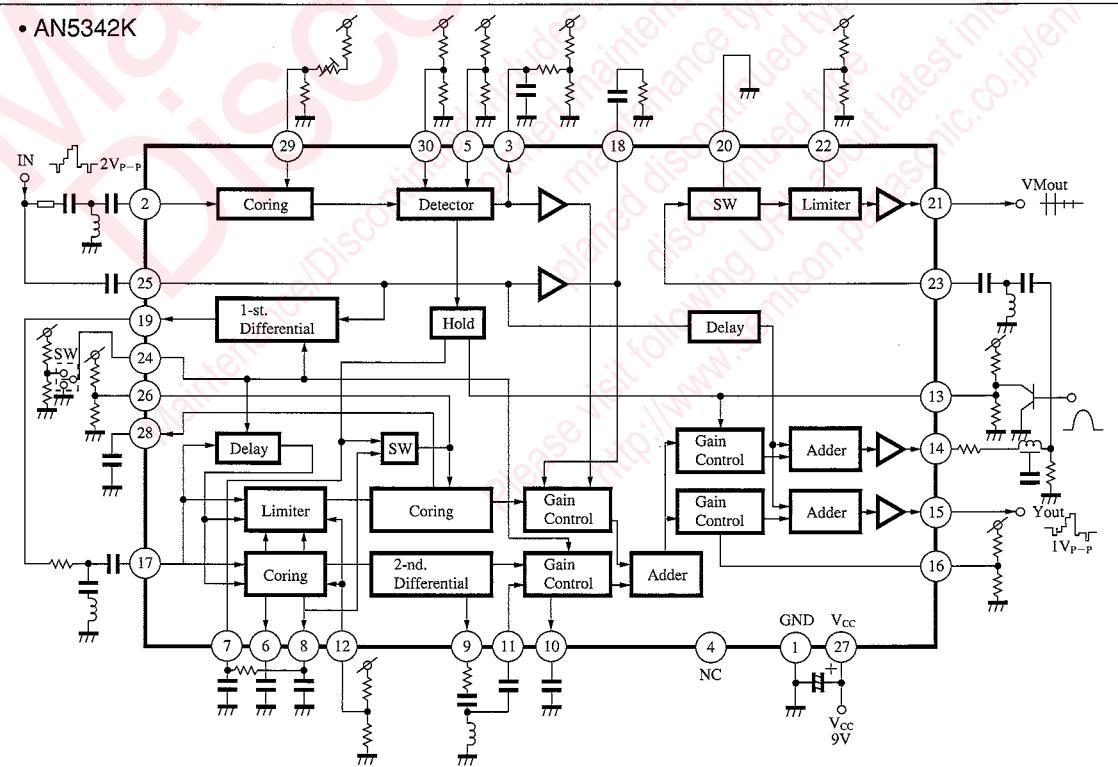
Parameter	Symbol	Range
Operating supply voltage range	V <sub>CC</sub>	8.1V to 10.8V

## ■ Block Diagram

### • AN5342FBP



### • AN5342K



## ■ Pin Descriptions

### • AN5342FBP

Pin No.	Pin name	Pin No.	Pin name
1	GND (lead frame)	23	GND (lead frame)
2	DSC large signal gain control	24	Pre-correction first differential output
3	Differential signal bias 1	25	Test Pin
4	Noise reduction bias	26	VM output
5	Differential signal bias 2	27	VM limiter control
6	GND (lead frame)	28	GND (lead frame)
7	Post-correction First Differential output	29	VM input
8	Apert. corr. Bias	30	Delay time switching
9	Second differential input	31	Y input
10	Apert. corr./detail level control	32	Detail coring control
11	GND (lead frame)	33	GND (lead frame)
12	GND (lead frame)	34	GND (lead frame)
13	VM peaking control	35	V <sub>CC</sub>
14	Y output for VM	36	Coring Bias
15	NC	37	DSC bias
16	NC	38	DSC small signal gain control
17	GND (lead frame)	39	GND (lead frame)
18	Y output	40	NC
19	Sharpness control	41	GND (main)
20	Pre-correction first differential input	42	DSC input
21	Brightness detection	43	DSC Detection output
22	GND (lead frame)	44	GND (lead frame)

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### • AN5342K

Pin No.	Pin name	Pin No.	Pin name
1	GND	16	Sharpness control
2	DSC input	17	Pre-correction first differential input
3	DSC detection output	18	Brightness Detection
4	NC	19	Pre-correction first differential output
5	DSC large signal Gain control	20	Test
6	Differential signal Bias 1	21	VM output
7	Noise reduction bias	22	VM limiter control
8	Differential signal Bias 2	23	VM input
9	Post-correction first differential output	24	Delay time switching
10	Aperture correction bias	25	Y input
11	Second differential input	26	Detail coring control
12	Aperture correction/detail separation level control	27	V <sub>CC</sub>
13	VM peaking control	28	Coring bias
14	Y output for VM	29	DSC bias
15	Y output	30	DSC small signal gain control

## ■ Electrical Characteristics ( $T_a=25\pm2^\circ\text{C}$ ) (AN5342FBP)

Parameter	Symbol	Condition	min	typ	max	Unit
Circuit current	I <sub>35</sub>		44	55	66	mA
	I <sub>19</sub>		0.4	0.7	1.2	mA
Circuit voltage	V <sub>42-41</sub>		2.3	2.7	3.1	V
	V <sub>2-41</sub>		4.4	4.8	5.2	V
	V <sub>10-41</sub>		2.7	3.1	3.5	V
	V <sub>3-41</sub>		2.6	3.2	3.8	V
	V <sub>5-41</sub>		2.6	3.2	3.8	V
	V <sub>7-41</sub>		1.8	2.4	3.0	V
	V <sub>8-41</sub>		2.9	3.5	4.1	V
	V <sub>9-41</sub>		2.3	2.7	3.1	V
	V <sub>13-41</sub>		2.7	3.1	3.5	V
	V <sub>14-41</sub>		3.1	3.7	4.3	V
	V <sub>18-41</sub>		3.1	3.7	4.3	V
	V <sub>20-41</sub>		4.4	4.9	5.3	V
	V <sub>21-41</sub>		3.6	4.0	4.4	V
	V <sub>24-41</sub>		5.5	6.1	6.7	V
	V <sub>26-41</sub>		7.5	8.1	8.6	V
	V <sub>27-41</sub>		2.2	2.6	3.0	V
	V <sub>29-41</sub>		1.9	2.3	2.7	V
	V <sub>31-41</sub>		4.1	4.5	4.9	V
	V <sub>32-41</sub>		5.0	5.4	5.8	V
	V <sub>36-41</sub>		5.0	5.6	6.2	V
	V <sub>38-41</sub>		3.9	4.3	4.7	V
Y signal voltage gain (1)	ΔV <sub>18-41</sub>	ΔV <sub>18</sub> at ΔV <sub>31</sub> =1V	420	500	580	mV
Y signal voltage gain (2)	ΔV <sub>14-41</sub>	ΔV <sub>14</sub> at ΔV <sub>31</sub> =1V	420	500	580	mV
Y signal voltage gain (3)	ΔV <sub>21-41</sub>	ΔV <sub>21</sub> at ΔV <sub>31</sub> =1V	0.95	1.1	1.25	V
<b>Delay Section</b>						
Y signal delay time	t <sub>DL</sub> (Y)	Y signal input, output delay time at DL=100ns	188	235	282	ns
Y signal frequency characteristics (1)	e <sub>f(Y1)</sub>	f=10MHz/f=1MHz at DL=100ns	-6	-4	—	dB
Y signal frequency characteristics (2)	e <sub>f(Y2)</sub>	f=10MHz/f=1MHz at DL=65ns	-6	-3	—	dB
Primary differential signal delay time	t <sub>DL</sub>	DL=100ns	80	100	120	ns
Primary differential signal delay time varying amount	Δt <sub>DL</sub>	Difference at delay time change over	28	35	42	ns
<b>Aperture Correction Section</b>						
Aperture correction signal maximum gain	A <sub>v(L)</sub>	f=2MHz Output at Vin=0.5V <sub>P-P</sub>	0.7	0.9	1.3	V <sub>P-P</sub>
Aperture correction signal coring characteristics (1)	e <sub>CO(L1)</sub>	f=4MHz, Vin=75mV <sub>P-P</sub> Output amplitude at V <sub>10</sub> =1V	100	130	160	mV <sub>P-P</sub>
Aperture correction signal coring characteristics (2)	e <sub>CO(L2)</sub>	f=4MHz, Vin=75mV <sub>P-P</sub> Output amplitude at V <sub>10</sub> =5V	—	25	50	mV <sub>P-P</sub>
Aperture correction signal secondary differential gain ratio	ΔA <sub>v'(L)</sub>	f=4Hz/f=2MHz at Vin=0.5V <sub>P-P</sub>	-6	-4	-2	dB
<b>Detail Correction Section</b>						
Detail correction signal maximum gain	A <sub>v(S)</sub>	f=4MHz Input output ratio at Vin=50mV <sub>P-P</sub>	16	18	21	dB

■ Electrical Characteristics (cont.) ( $T_a = 25 \pm 2^\circ\text{C}$ ) (AN5342FBP)

Parameter	Symbol	Condition	min	typ	max	Unit
Detail correction signal gain control (typ.)	$\Delta A_v(s)$	$f=4\text{MHz}$ $V_{in}=50\text{mV}_{\text{P-P}}$ Output ratio at $V_{43}=5\text{V} \rightarrow 3\text{V}$	-8.5	-6	-3.5	dB
Detail correction signal coring characteristics	$e_{CO}(s)$	$f=4\text{MHz}$ $V_{in}=50\text{mV}_{\text{P-P}}$ Output ratio at $V_{32}=5\text{V} \rightarrow 3\text{V}$	-7	-4	-2	dB
Detail correction signal limiter characteristics	$\Delta e_{LT}(s)$	$f=4\text{MHz}$ $V_{in}=100\text{mV}_{\text{P-P}}$ Output ratio at $V_{10}=5\text{V} \rightarrow 3\text{V}$	—	-5	-3	dB
Detail correction signal sharpness control	$\Delta A_{v'}(s)$	$f=4\text{MHz}$ $V_{in}=50\text{mV}_{\text{P-P}}$ Output ratio at $V_{19}=5\text{V} \rightarrow 3\text{V}$	—	-7	-4	dB
<b>DSC Section</b>						
DSC output voltage (1)	$V_{LIM(DSC)}$	$f=4\text{MHz}$ Output DC at $V_{in}=27\text{mV}_{\text{P-P}}$	2	3	4	V
DSC output voltage (2)	$V_S(DSC)$	$f=4\text{MHz}$ Output DC at $V_{in}=150\text{mV}_{\text{P-P}}$	7.5	8.8	—	V
DSC output voltage (3)	$V_L(DSC)$	$f=4\text{MHz}$ Output DC at $V_{in}=840\text{mV}_{\text{P-P}}$	—	0.2	1.0	V
Noise reduction characteristics	$V_{NR}$	$f=4\text{MHz}$ Pin <sup>②</sup> bias voltage at $V_{in}=150\text{mV}_{\text{P-P}}$	—	0.2	1.0	V
<b>VM Section</b>						
VM signal maximum gain	$A_v(VM)$	$f=4\text{MHz}$ Output amplitude at $V_{in}=100\text{mV}_{\text{P-P}}$	0.6	0.9	1.4	$\text{V}_{\text{P-P}}$
VM signal limiter characteristics	$\Delta A_v(VM)$	$f=4\text{MHz}$ $V_{in}=100\text{mV}_{\text{P-P}}$ Output ratio at $V_{27}=5\text{V} \rightarrow 3\text{V}$	2.5	4.0	5.5	dB
VM signal SW operation characteristics	$e_{off}(VM)$	$f=4\text{MHz}$ $V_{in}=100\text{mV}_{\text{P-P}}$ Output ratio at $V_{25}=0 \rightarrow 2\text{V}$	—	-40	-25	dB
VM signal output DC level	$V_{26-41}$	Difference in case between, $V_{25}=0$ and $V_{25}=2\text{V}$	-90	0	+90	mV
<b>Reference Value</b>						
Y signal delay time variation amount	$\Delta t_{DL}(Y)$	Delay time difference in delay time changeover	—	(35)	—	ns
Primary differential signal pulse width (1)	$\Delta t_{(DL_1)}$	Output amplitude at 125ns rise pulse inputs ( $DL=100\text{ns}$ )	—	(190)	—	ns
Primary differential signal pulse width (2)	$\Delta t_{(DL_2)}$	Output amplitude at 125ns rise pulse inputs ( $DL=65\text{ns}$ )	—	(225)	—	ns
Primary differential signal output amplitude (1)	$A_v(DL_1)$	Output amplitude at 125ns rise pulse inputs ( $DL=100\text{ns}$ )	—	(0.9)	—	$\text{V}_{\text{P-P}}$
Primary differential signal output amplitude (2)	$A_v(DL_2)$	Output amplitude at 125ns rise pulse inputs ( $DL=65\text{ns}$ )	—	(0.8)	—	$\text{V}_{\text{P-P}}$
Aperture correction signal gain difference at delay change-over	$\Delta A_v(L)$	$f=2\text{MHz}$ , $V_{in}=0.5\text{V}_{\text{P-P}}$ Output ratio at $V_{30}=0 \rightarrow 3\text{V}$	—	(-3)	—	dB

Note) The characteristics value in parentheses is not a guaranteed value, but reference one on design.

### ■ Electrical Characteristics (Ta=25±2°C) (AN5342K)

Parameter	Symbol	Condition	min	typ	max	Unit
Circuit current	I <sub>27</sub>		44	55	66	mA
	I <sub>16</sub>		0.4	0.7	1.2	mA
Circuit voltage	V <sub>2-1</sub>		2.3	2.7	3.1	V
	V <sub>5-1</sub>		4.4	4.8	5.2	V
	V <sub>12-1</sub>		2.7	3.1	3.5	V
	V <sub>6-1</sub>		2.6	3.2	3.8	V
	V <sub>8-1</sub>		2.6	3.2	3.8	V
	V <sub>9-1</sub>		1.8	2.4	3.0	V
	V <sub>10-1</sub>		2.9	3.5	4.1	V
	V <sub>11-1</sub>		2.3	2.7	3.1	V
	V <sub>13-1</sub>		2.7	3.1	3.5	V
	V <sub>14-1</sub>		3.1	3.7	4.3	V
	V <sub>15-1</sub>		3.1	3.7	4.3	V
	V <sub>17-1</sub>		4.4	4.9	5.3	V
	V <sub>18-1</sub>		3.6	4.0	4.4	V
	V <sub>19-1</sub>		5.5	6.1	6.7	V
	V <sub>21-1</sub>		7.5	8.1	8.6	V
	V <sub>22-1</sub>		2.2	2.6	3.0	V
	V <sub>23-1</sub>		1.9	2.3	2.7	V
	V <sub>25-1</sub>		4.1	4.5	4.9	V
	V <sub>26-1</sub>		5.0	5.4	5.8	V
	V <sub>28-1</sub>		5.0	5.6	6.2	V
	V <sub>30-1</sub>		3.9	4.3	4.7	V
Y signal voltage gain (1)	ΔV <sub>15-1</sub>	ΔV <sub>15</sub> at ΔV <sub>25</sub> =1V	420	500	580	mV
Y signal voltage gain (2)	ΔV <sub>14-1</sub>	ΔV <sub>14</sub> at ΔV <sub>25</sub> =1V	420	500	580	mV
Y signal voltage gain (3)	ΔV <sub>18-1</sub>	ΔV <sub>18</sub> at ΔV <sub>25</sub> =1V	0.95	1.1	1.25	V
<b>Delay Section</b>						
Y signal delay time	t <sub>DL</sub> (Y)	Y signal input, output delay time at DL=100ns	188	235	282	ns
Y signal frequency characteristics (1)	e <sub>f</sub> (Y <sub>1</sub> )	f=10MHz/f=1MHz at DL=100ns	-6	-4	—	dB
Y signal frequency characteristics (2)	e <sub>f</sub> (Y <sub>2</sub> )	f=10MHz/f=1MHz at DL=65ns	-6	-3	—	dB
Primary differential signal delay time	t <sub>DL</sub>	DL = 100ns	80	100	120	ns
Primary differential signal delay time varying amount	Δt <sub>DL</sub>	Difference in delay time change-over	28	35	42	ns
<b>Aperture Correction Section</b>						
Aperture correction signal maximum gain	A <sub>v</sub> (L)	f=2MHz Output at Vin=0.5V <sub>P-P</sub>	0.7	0.9	1.3	V <sub>P-P</sub>
Aperture correction signal coring characteristics (1)	e <sub>CO</sub> (L <sub>1</sub> )	f=4MHz, Vin=75mV <sub>P-P</sub> Output amplitude at V <sub>12</sub> =1V	100	130	160	mV <sub>P-P</sub>
Aperture correction signal coring characteristics (2)	e <sub>CO</sub> (L <sub>2</sub> )	f=4MHz, Vin=75mV <sub>P-P</sub> Output amplitude at V <sub>12</sub> =5V	—	25	50	mV <sub>P-P</sub>
Aperture correction signal secondary differential gain ratio	ΔA <sub>v'</sub> (L)	f=4MHz/f=2MHz at Vin=0.5V <sub>P-P</sub>	-6	-4	-2	dB
<b>Detail Correction Section</b>						
Detail correction signal maximum gain	A <sub>v</sub> (S)	Input output ratio at Vin=50mV <sub>P-P</sub>	16	18	21	dB
Detail correction signal gain control (typ.)	ΔA <sub>v</sub> (S)	Output ratio at V <sub>3</sub> =5V→3V	-8.5	-6	-3.5	dB

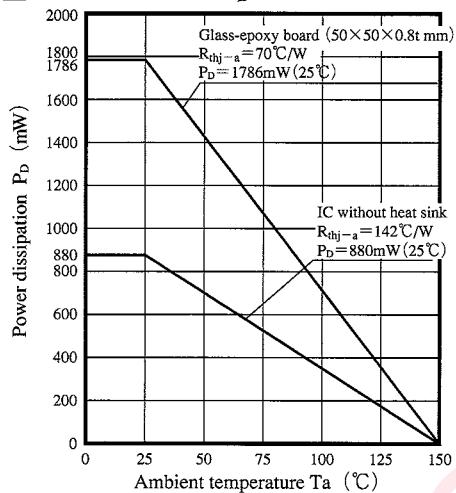
## ■ Electrical Characteristics (cont.) (Ta=25±2°C) (AN5342K)

Parameter	Symbol	Condition	min	typ	max	Unit
Detail correction signal coring characteristics	$e_{CO}$ (s)	f=4MHz, Vin=50mV <sub>P-P</sub> Output ratio at V <sub>26</sub> =5V→3V	-7	-4	-2	dB
Detail correction signal limiter characteristics	$\Delta e_{LT}$ (s)	f=4MHz, Vin=100mV <sub>P-P</sub> Output ratio at V <sub>12</sub> =5V→3V	—	-5	-3	dB
Detail correction signal sharpness control	$\Delta A_{S'}$ (s)	f=4MHz, Vin=50mV <sub>P-P</sub> Output ratio at V <sub>16</sub> =5V→3V	—	-7	-4	dB
<b>DSC Section</b>						
DSC output voltage (1)	V <sub>LIM (DSC)</sub>	f=4MHz Output DC at Vin=27mV <sub>P-P</sub>	2	3	4	V
DSC output voltage (2)	V <sub>S (DSC)</sub>	f=4MHz, Output DC at Vin=150mV <sub>P-P</sub>	7.5	8.8	—	V
DSC output voltage (3)	V <sub>L (DSC)</sub>	f=4MHz, Output DC at Vin=840mV <sub>P-P</sub>	—	0.2	1.0	V
Noise reduction characteristics	V <sub>NR</sub>	f=4MHz, Pin② bias voltage at Vin=150mV <sub>P-P</sub>	—	0.2	1.0	V
<b>VM Section</b>						
VM signal maximum gain	A <sub>v (VM)</sub>	f=4MHz, Output amplitude at Vin=100mV <sub>P-P</sub>	0.6	0.9	1.4	V <sub>P-P</sub>
VM signal limiter characteristics	$\Delta A_{v (VM)}$	f=4MHz, Vin=100mV <sub>P-P</sub> Output ratio at V <sub>22</sub> =0→2V	2.5	4.0	5.5	dB
VM signal SW operation characteristics	e <sub>off (VM)</sub>	f=4MHz, Vin=100mV <sub>P-P</sub> Output ratio at V <sub>20</sub> =5V→3V	—	-40	-25	dB
VM signal output DC level	$\Delta V_{21-1}$	V <sub>CC</sub> =9V, Pin② output voltage difference at V <sub>20</sub> =0V/2V	-90	0	+90	mV
<b>Reference Value</b>						
Y signal delay time variation amount	$\Delta t_{DL (Y)}$	Difference of delay time in delay time change-over	—	(35)	—	ns
Primary differential signal pulse width (1)	$\Delta t_{(DL_1)}$	Pulse width in 125ns pulse input (DL=100ns)	—	(190)	—	ns
Primary differential signal pulse width (2)	$\Delta t_{(DL_2)}$	Pulse width in 125ns pulse input (DL=65ns)	—	(225)	—	ns
Primary differential signal output amplitude (1)	A <sub>v (DL_1)</sub>	Pulse width in 125ns pulse input (DL=100ns)	—	(0.9)	—	V <sub>P-P</sub>
Primary differential signal output amplitude (2)	A <sub>v (DL_2)</sub>	Pulse width in 125ns pulse input (DL=65ns)	—	(0.8)	—	V <sub>P-P</sub>
Profile correction signal gain difference at delay change-over	$\Delta A_{v (L)}$	f=2MHz, Vin=0.5V <sub>P-P</sub> Output ratio at V <sub>24</sub> =0→3V	—	(-3)	—	dB

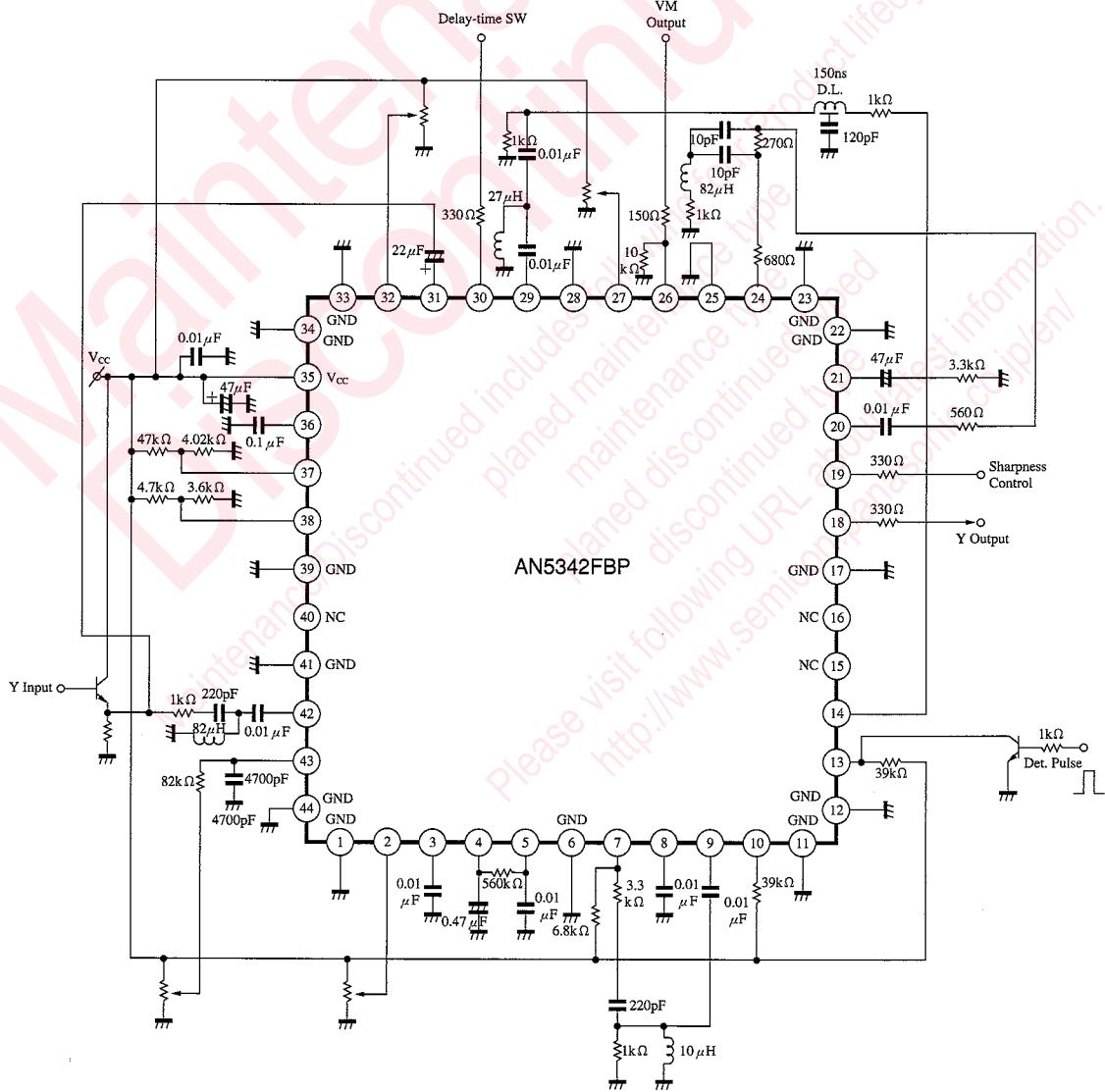
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Note) The characteristics value in parentheses is not a guaranteed value, but reference one on design.

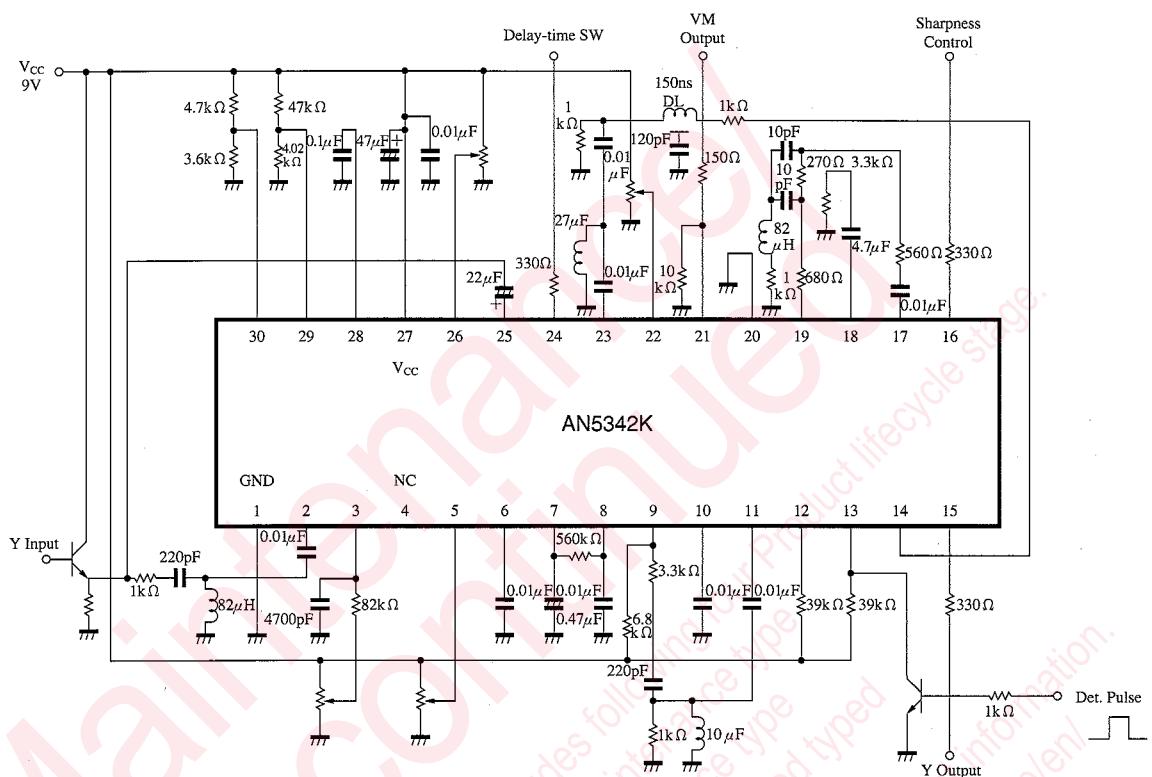
### ■ Reference $P_D - Ta$



### ■ Application Circuit of AN5342FBP



## ■ Application Circuit



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